

/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

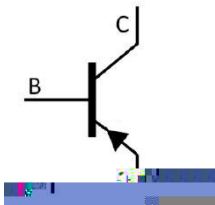
/ Features

h_{FE} , 2SD596
High h_{FE} , complementary pair with 2SD596.

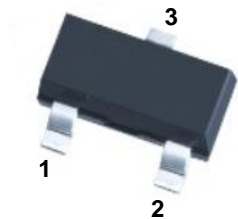
/ Applications

Audio frequency amplifier application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	1	2	3	4	5
h_{FE} Range	110 180	135 220	170 270	200 320	250 400
Marking	HBV1	HBV2	HBV3	HBV4	HBV5

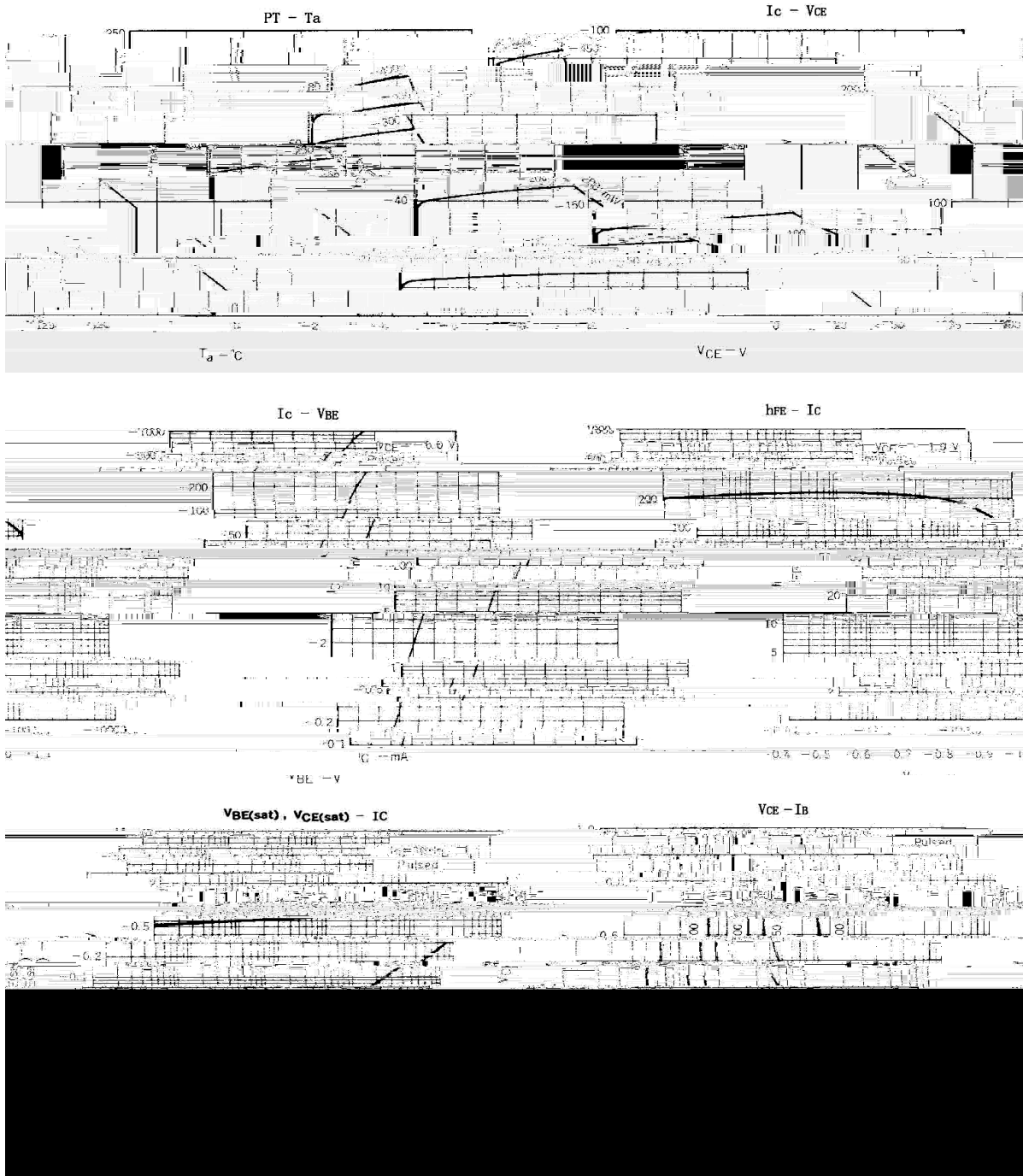
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-700	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

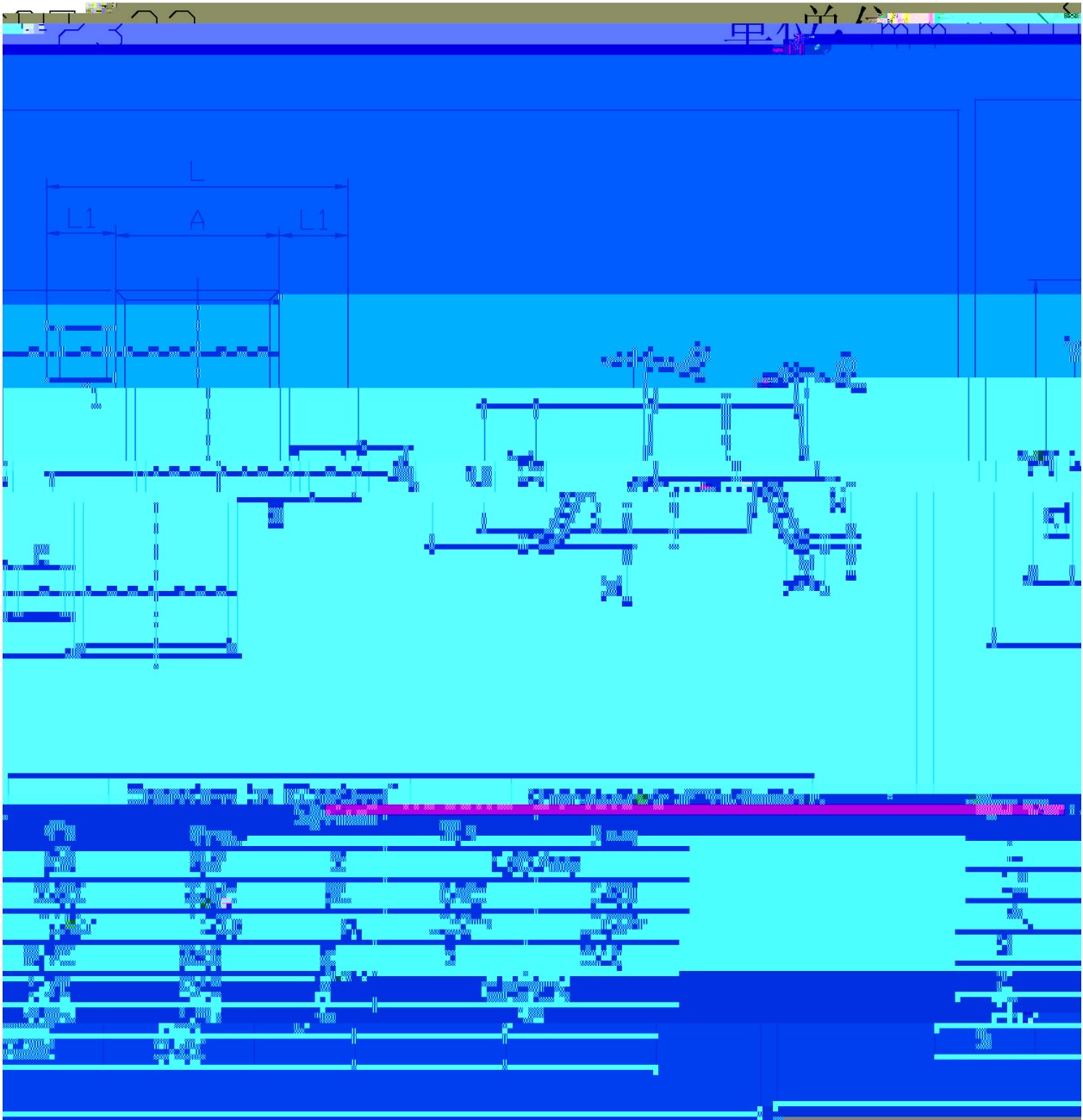
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-1.0V$ $I_C=-100mA$	110	200	400	
	$h_{FE(2)}$	$V_{CE}=-1.0V$ $I_C=-700mA$	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-700mA$ $I_B=-70mA$		-0.25	-0.6	V
Collector to Base Voltage	V_{BE}	$V_{CE}=-6.0V$ $I_C=-10mA$	-0.6	-0.64	-0.7	V
Transition Frequency	f_T	$V_{CE}=-6.0V$ $I_E=10mA$		160		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-6.0V$ $I_E=0$ $f=10MHz$		17		pF

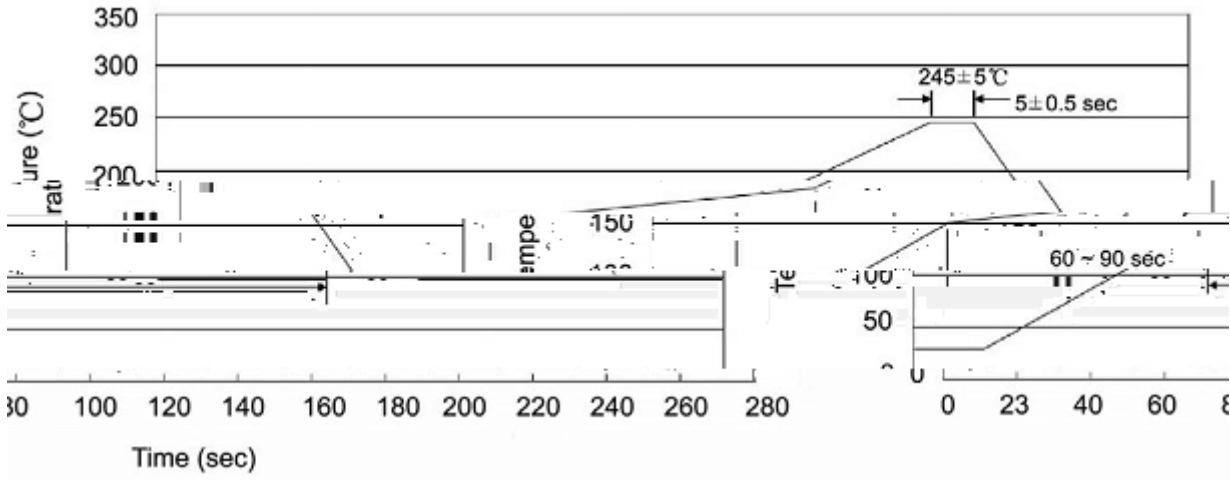
/ Electrical Characteristic Curve



/ Package Dimensions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60